Abstracts

Non-quasi-static large signal transient model for heterojunction bipolar transistors

---

A. Ouslimani, H. Hafdallah, M. Medjnoun, J. Gaubert and P. Pouvil. "Non-quasi-static large signal transient model for heterojunction bipolar transistors." 1999 MTT-S International Microwave Symposium Digest 99.2 (1999 Vol. II [MWSYM]): 427-430 vol.2.

A NQS large-signal transient HBT model is proposed. It is based on a QS model and includes the base push-out effects and the NQS effect associated with the transient regime of the distributed charges in the neutral base. The influence of the NQS effect is demonstrated in the picosecond transient regime.

❑ Return to main document.